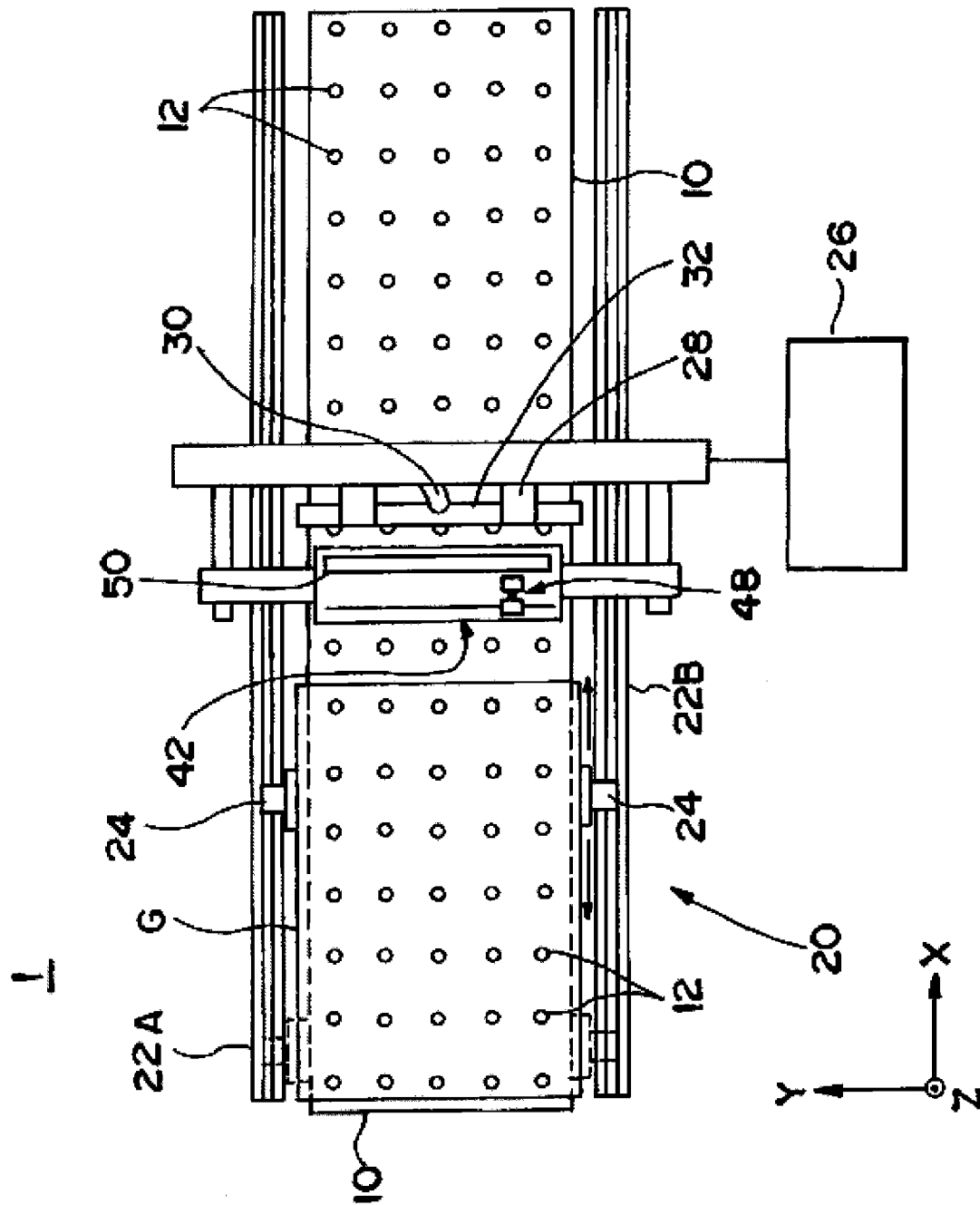
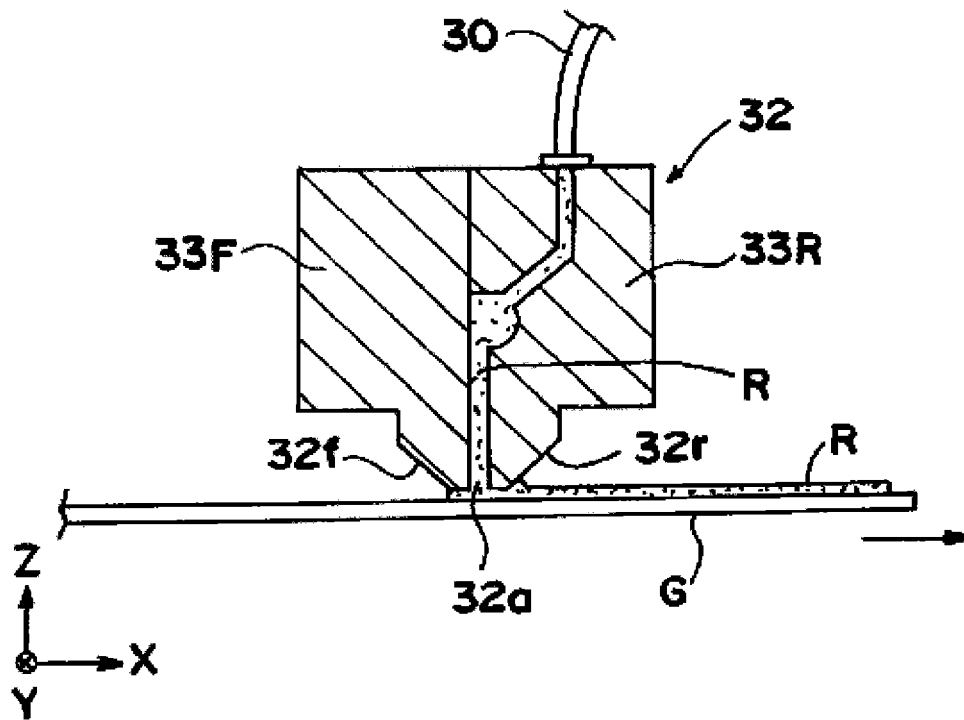


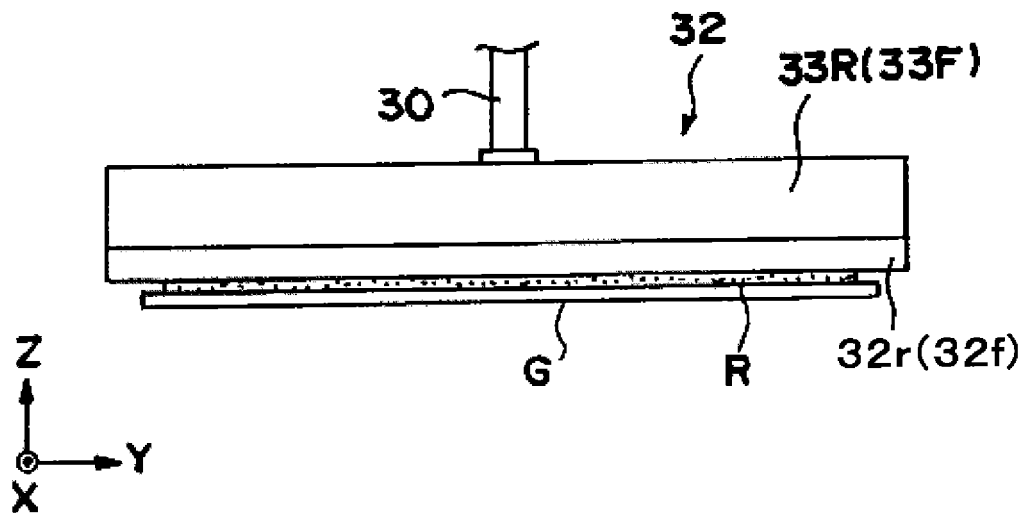
[図1]



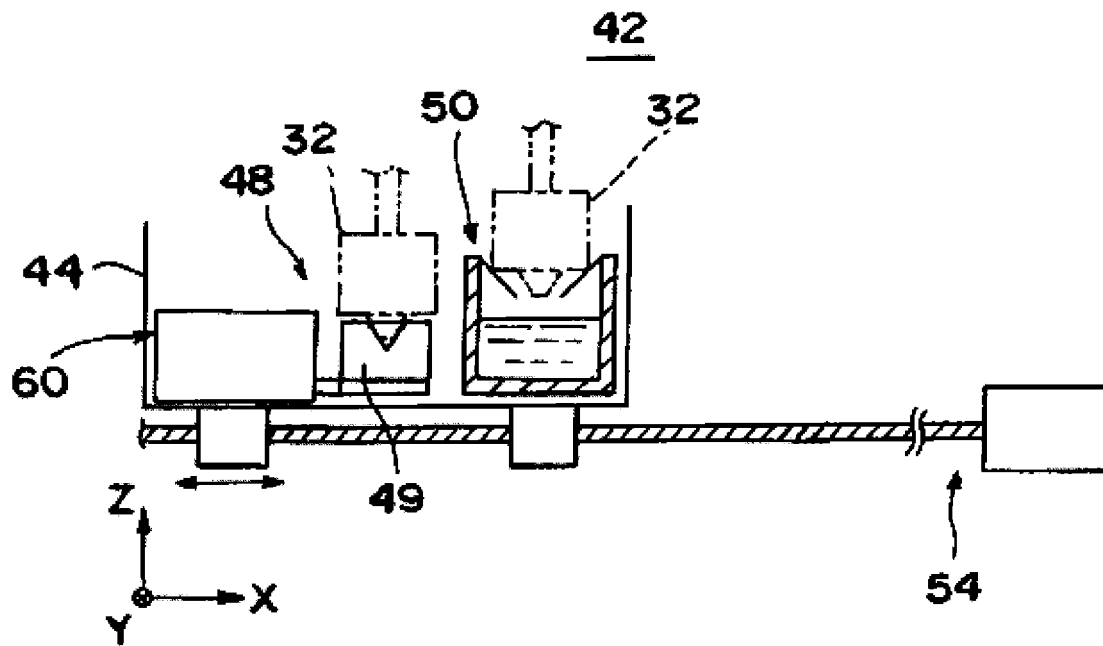
[図2]



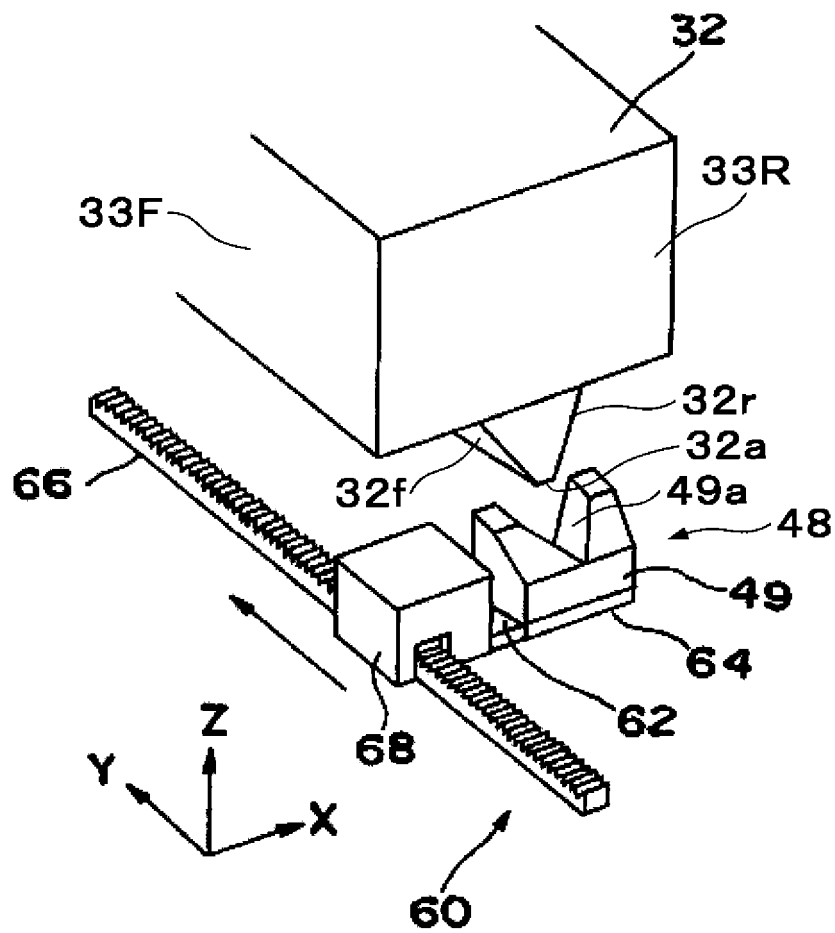
[図3]



[図4]

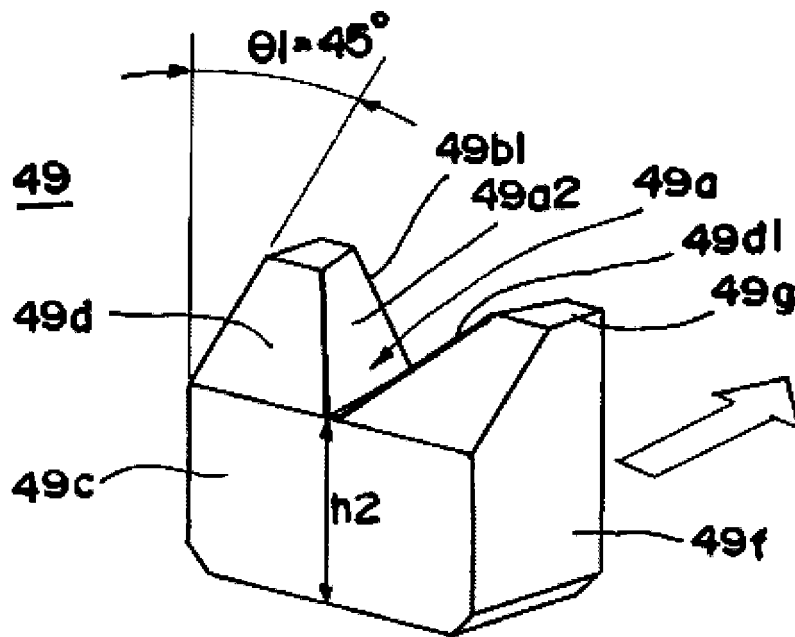


[図5]

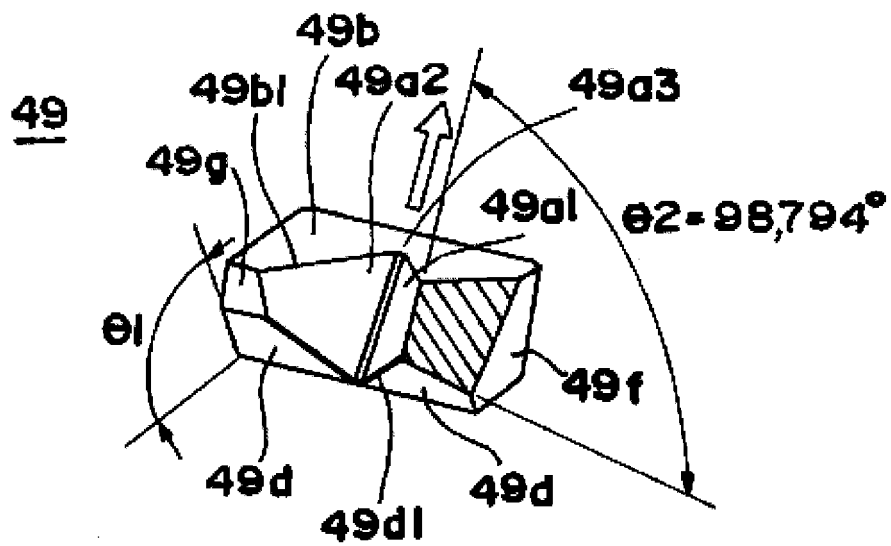


A cross-sectional view of a semiconductor device 49. The device consists of a substrate 49a1 with a central vertical channel 49a3. On either side of the channel, there are two layers: an inner layer 49a2 and an outer layer 49c. The top surface is labeled 49d. The bottom surface is labeled 49b. The side surfaces are labeled 49e and 49f. The bottom corners are labeled 49g. A large downward-pointing arrow is shown below the device, indicating a direction of force or process.

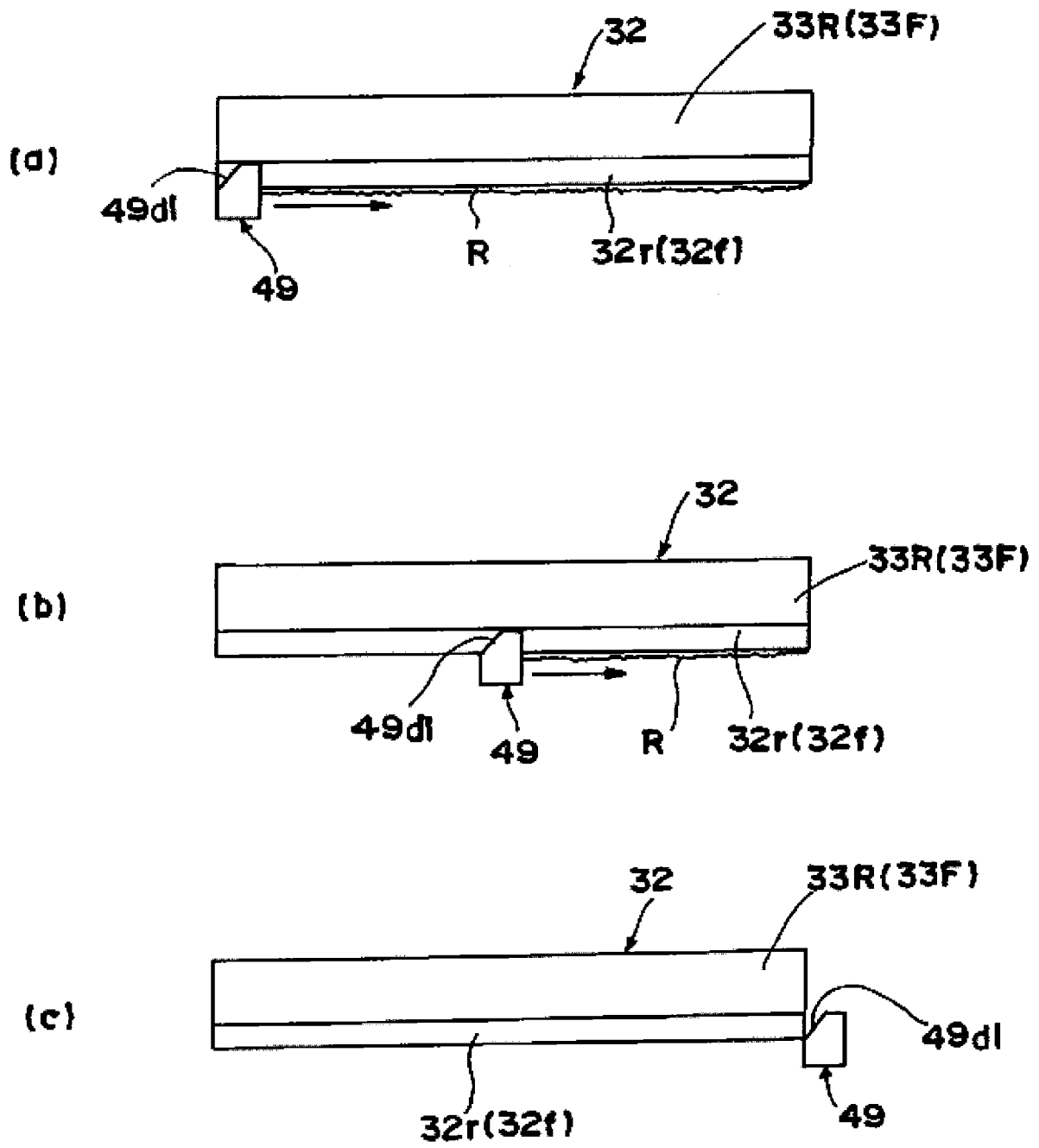
[図8]



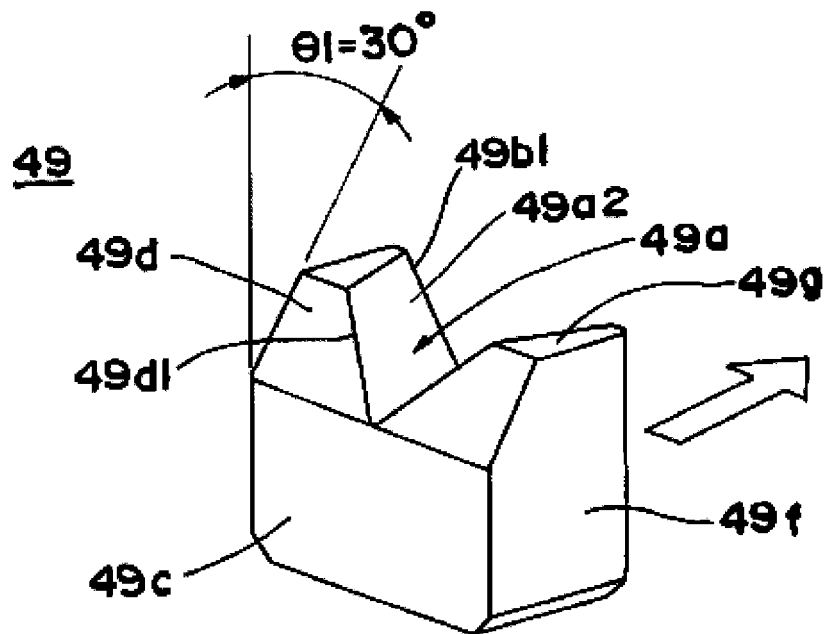
[図9]



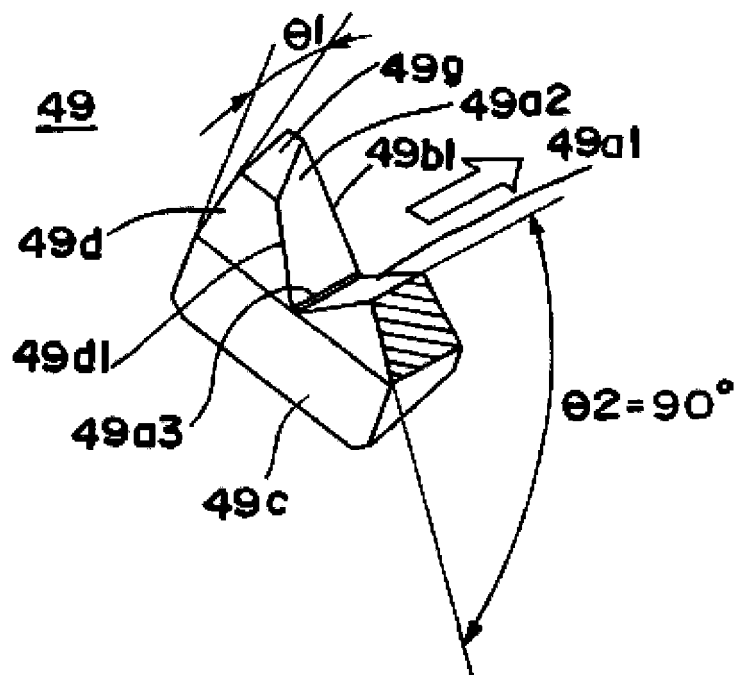
[図10]



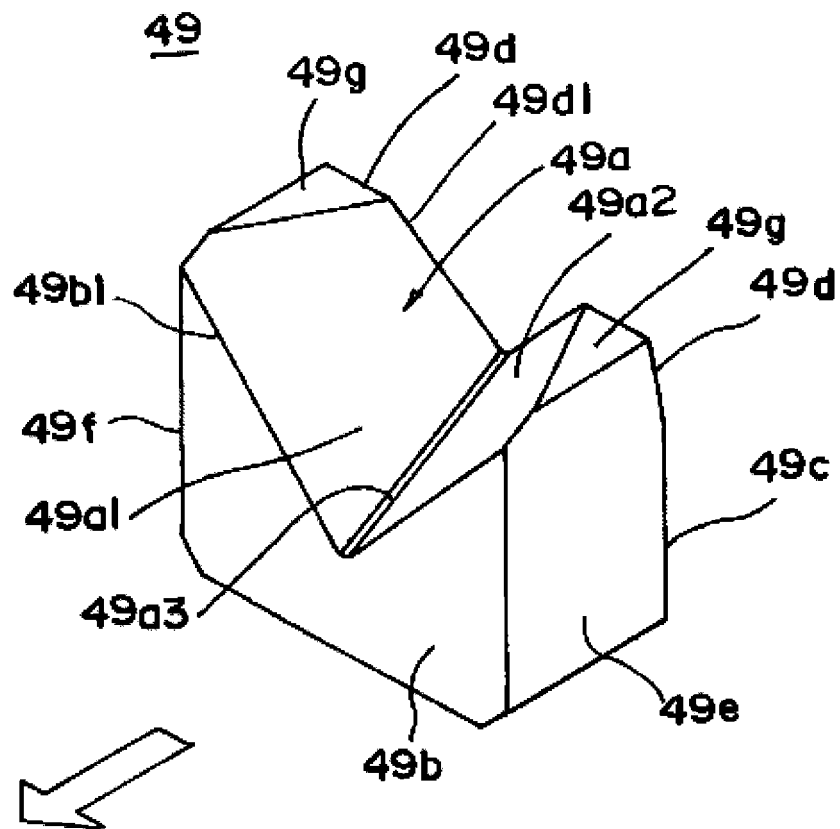
[図11]



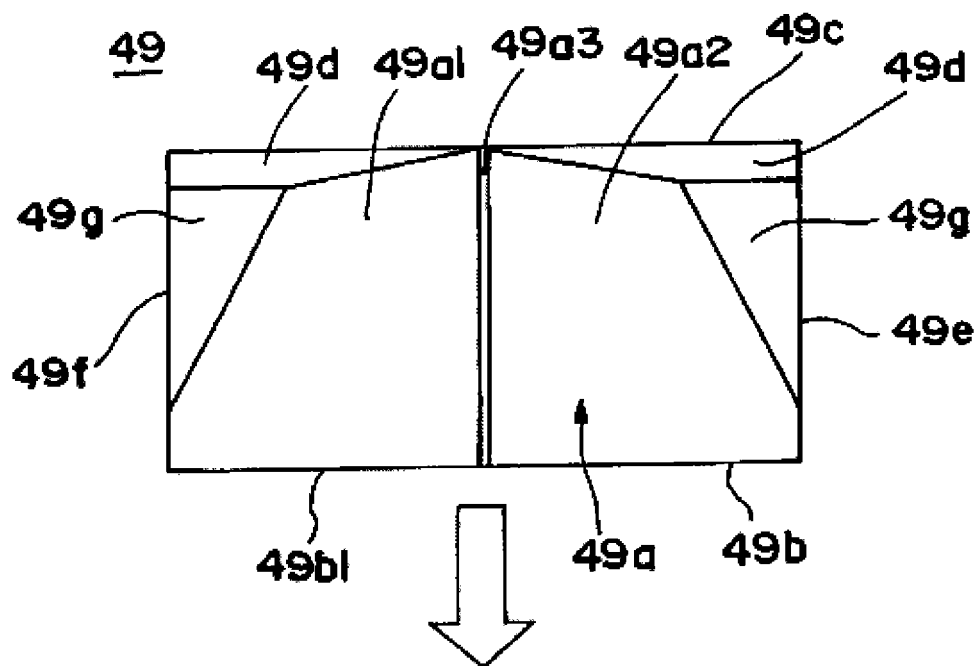
[図12]



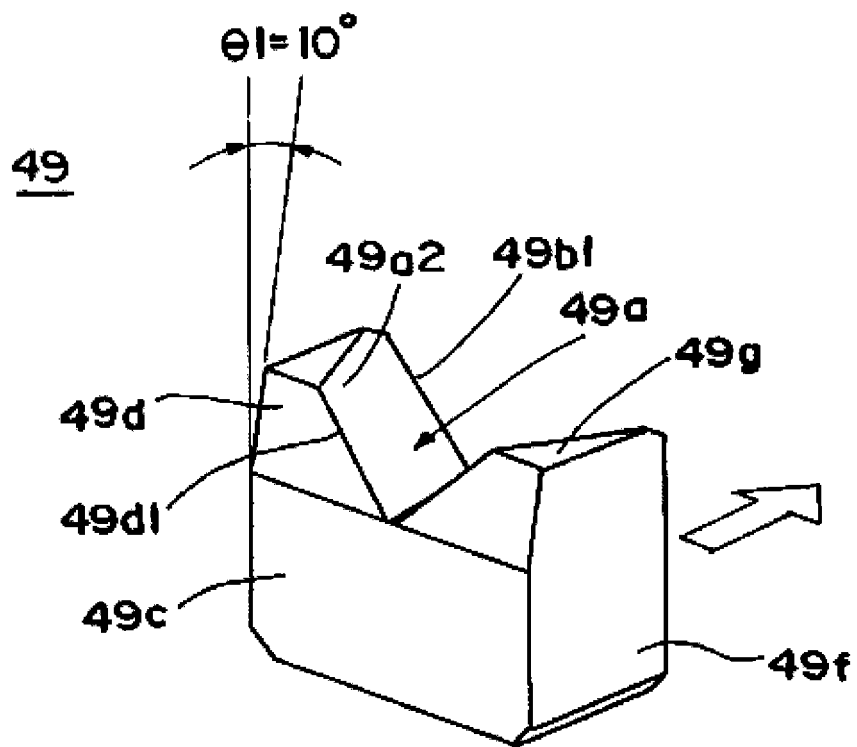
[図13]



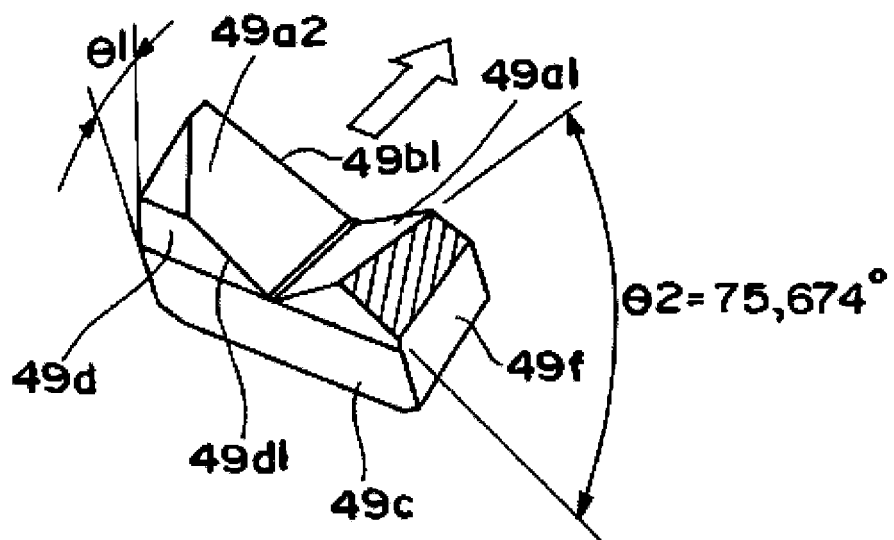
[図14]



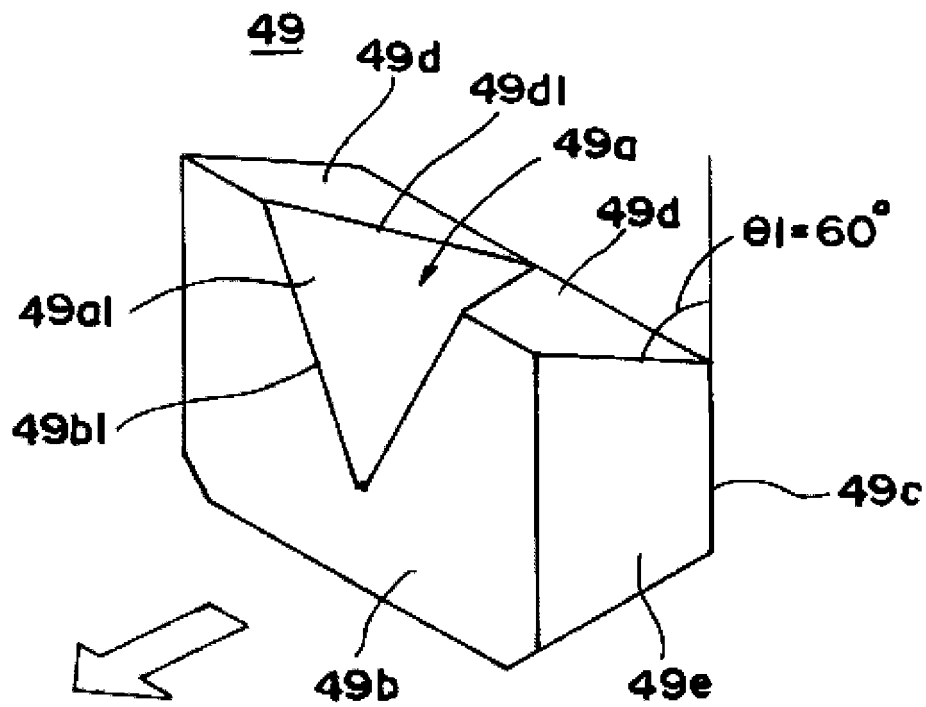
[図15]



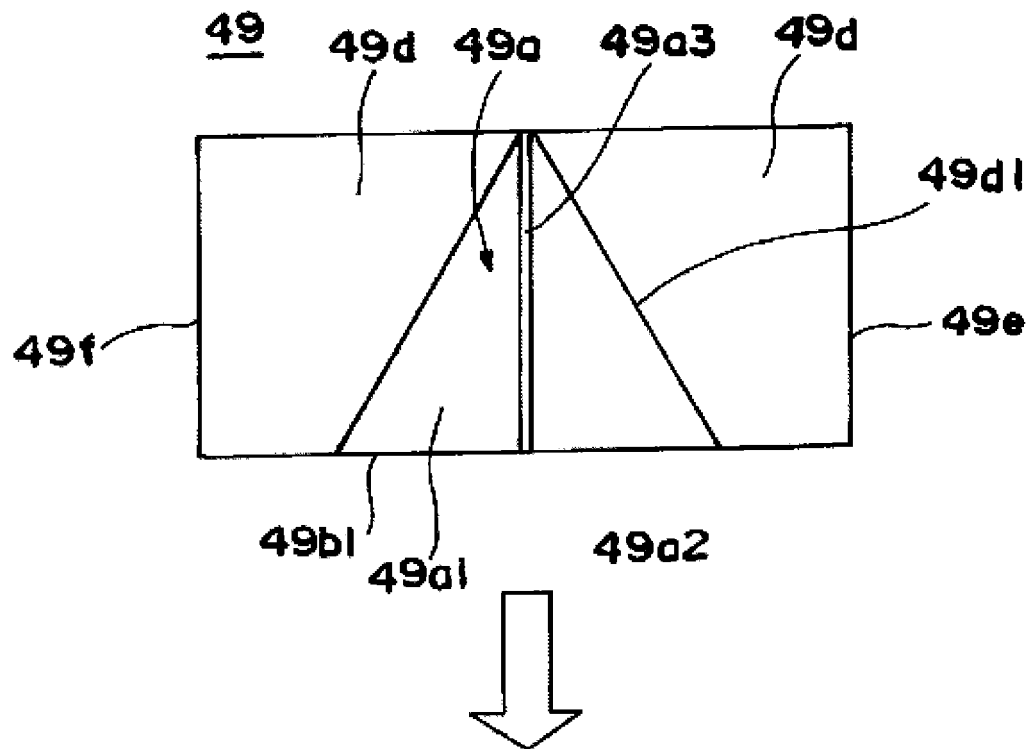
[図16]



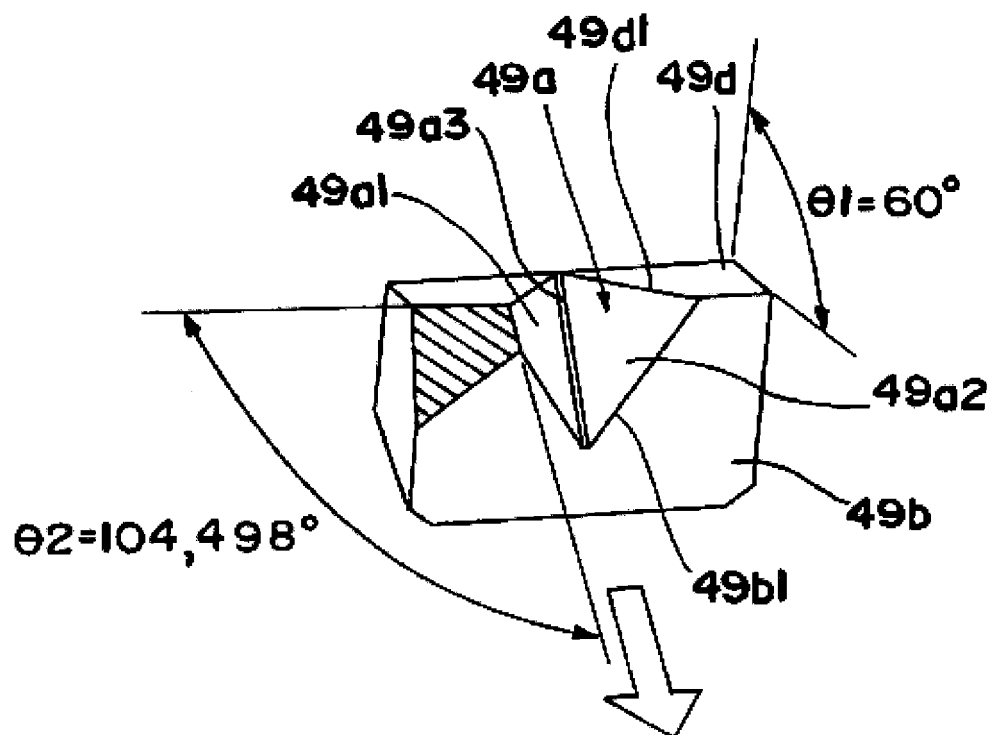
[図17]



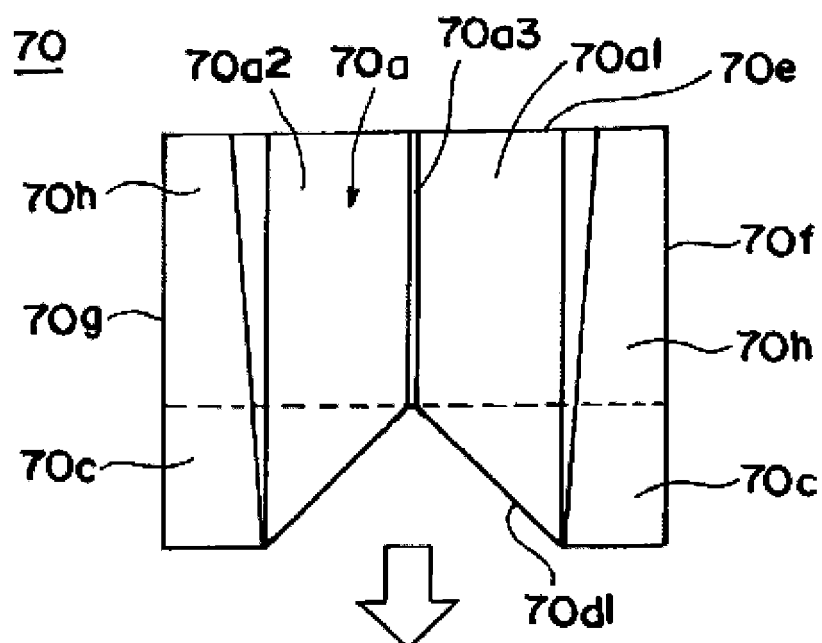
[図18]



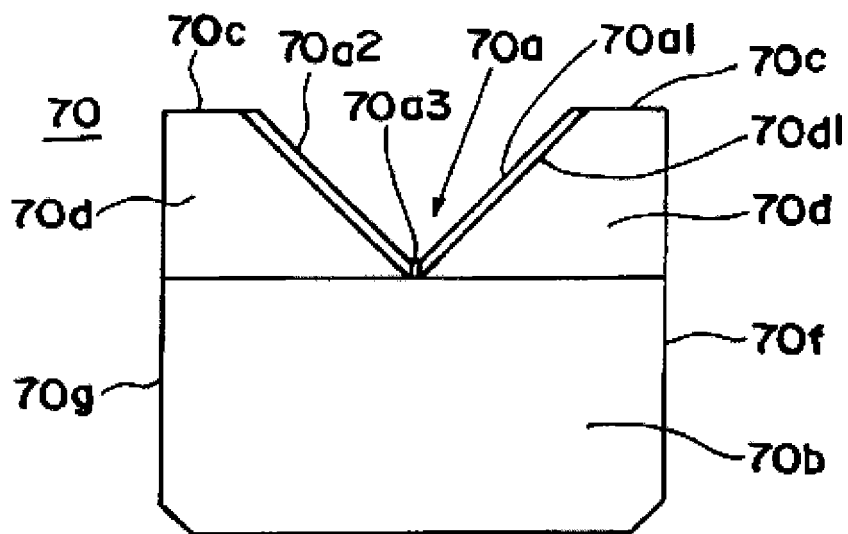
[図19]



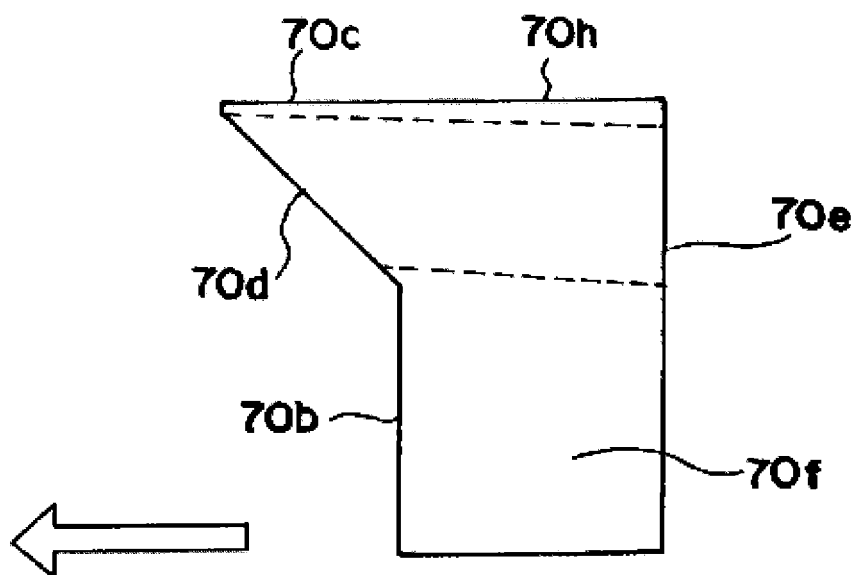
[図20]



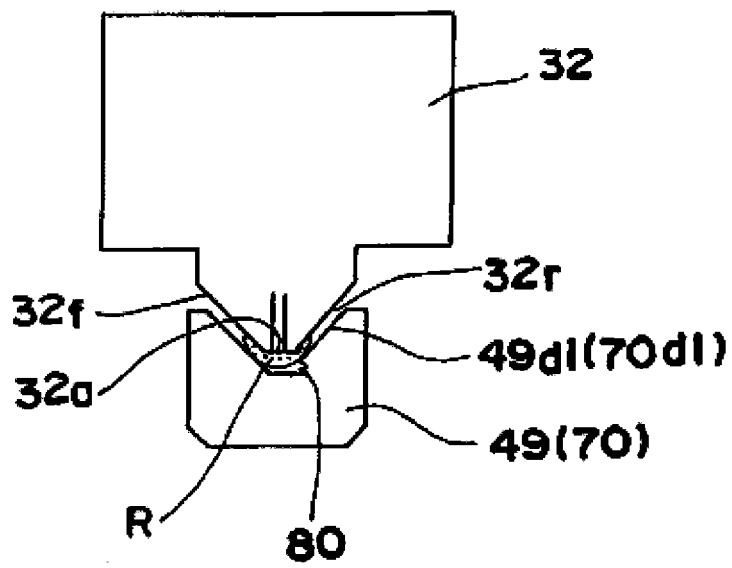
[図21]



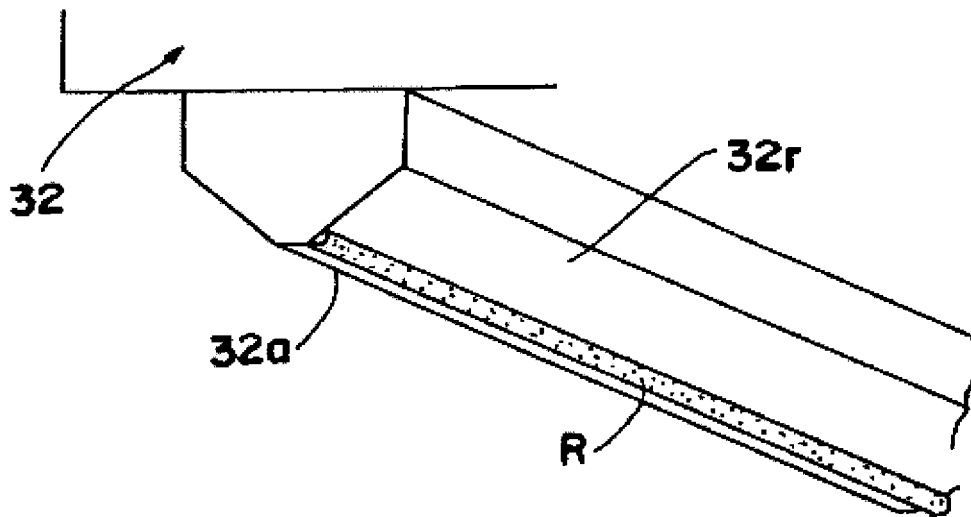
[図22]



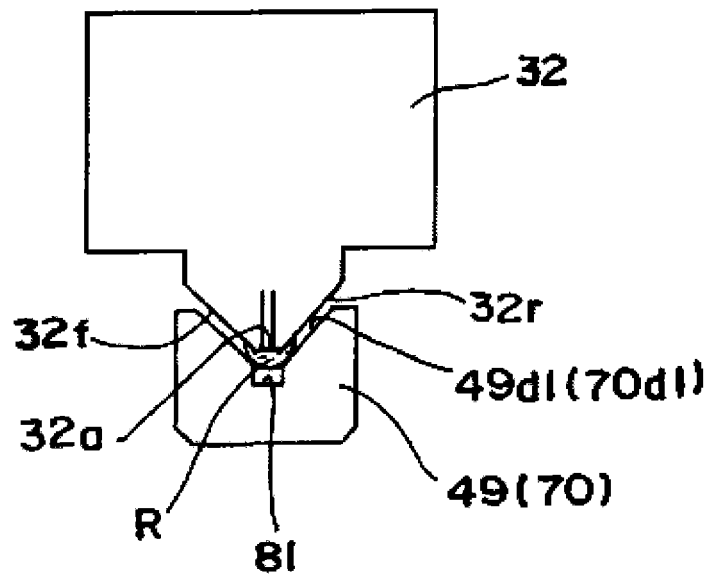
[図23]



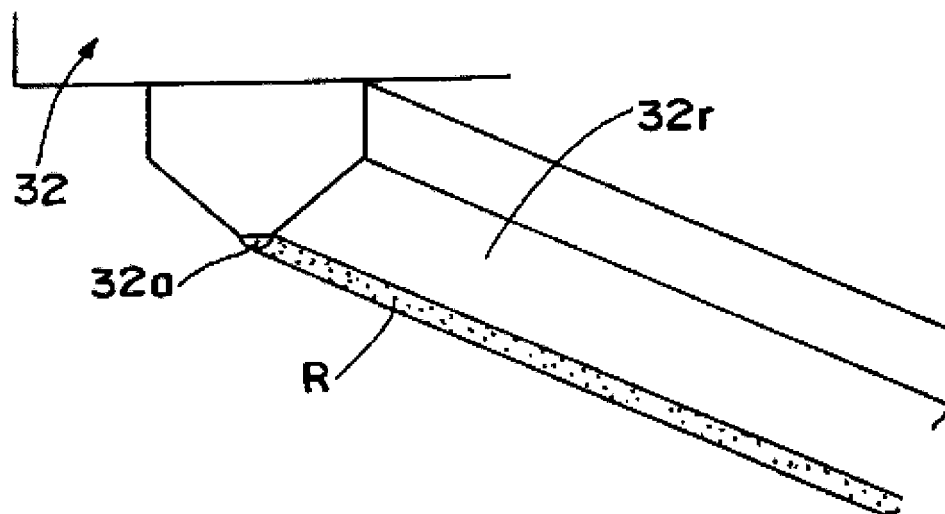
[図24]



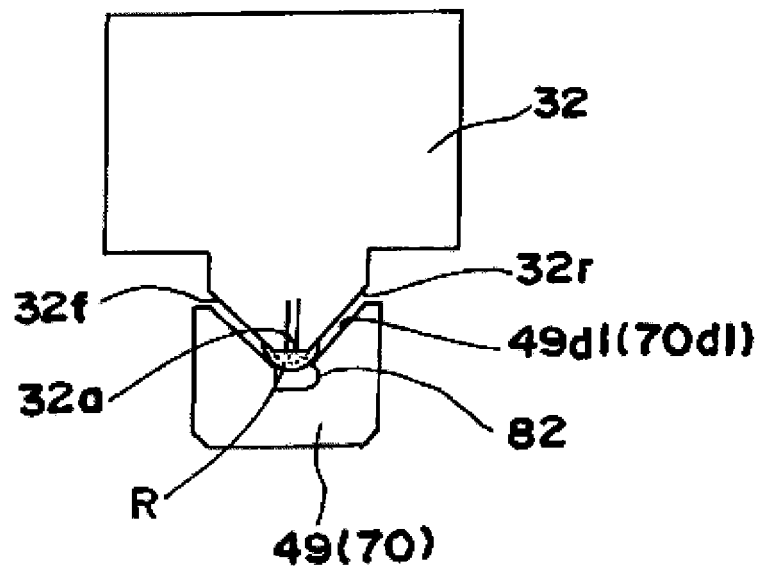
[図25]



[図26]



[図27]



[図28]

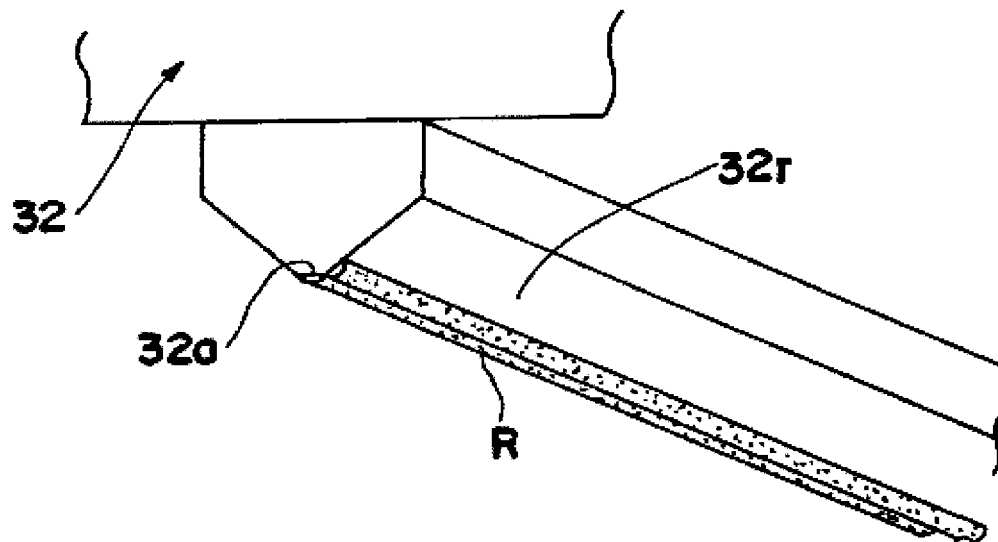
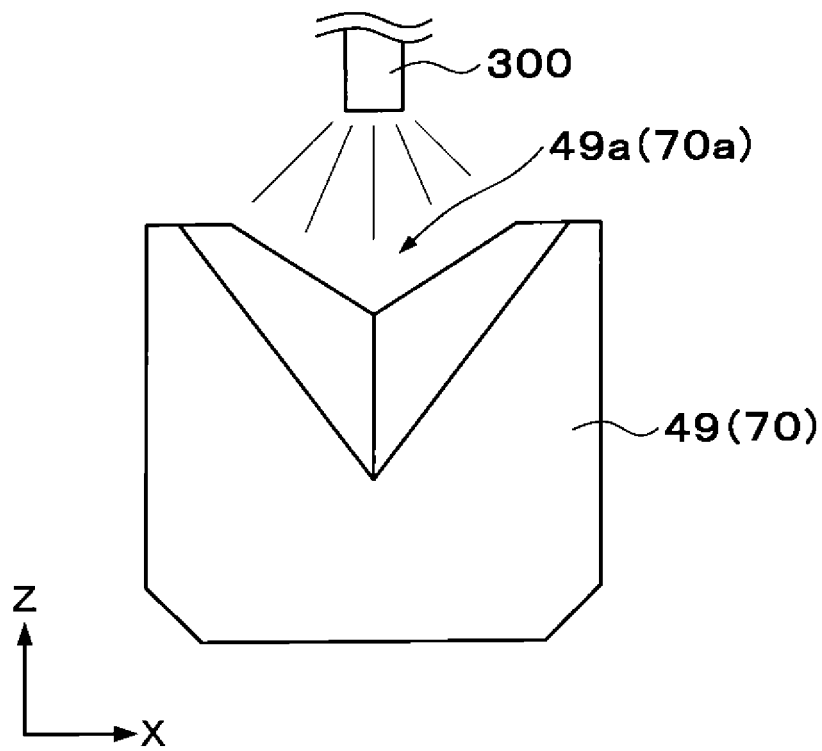


FIG. 1 is a perspective view of a rectangular block 202. The block has a wavy surface 202a along its bottom edge. A curved arrow R indicates a rotation around the longitudinal axis.

[図31]



[図32]

